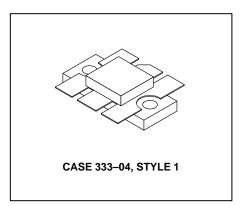
# The RF Line NPN Silicon RF Power Transistor

Designed primarily for wideband large-signal output and driver amplifier stages in the 400 to 512 MHz frequency range.

- Specified 28 Volt, 470 MHz Characteristics
   Output Power = 80 Watts
   Minimum Gain = 7.3 dB
   Efficiency = 50% (Min)
- Built-In Matching Network for Broadband Operation
- 100% Tested for Load Mismatch at all Phase Angles with 30:1 VSWR
- Gold Metallization System for High Reliability Applications

## **MRF338**

80 W, 400 to 512 MHz CONTROLLED "Q" BROADBAND RF POWER TRANSISTOR NPN SILICON



#### **MAXIMUM RATINGS**

Rating	S	ymbol	Value	Unit
Collector–Emitter Voltage	\	VCEO	30	Vdc
Collector-Base Voltage	\	V <sub>СВО</sub>	60	Vdc
Emitter–Base Voltage	\	VEBO	4	Vdc
Collector Current — Continuous — Peak		lC	9 12	Adc
Total Device Dissipation @ T <sub>C</sub> = 25°C (1) Derate above 25°C		PD	250 1.43	Watts W/°C
Storage Temperature Range		T <sub>stg</sub>	-65 to +150	°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (2)		0.7	°C/W

## **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

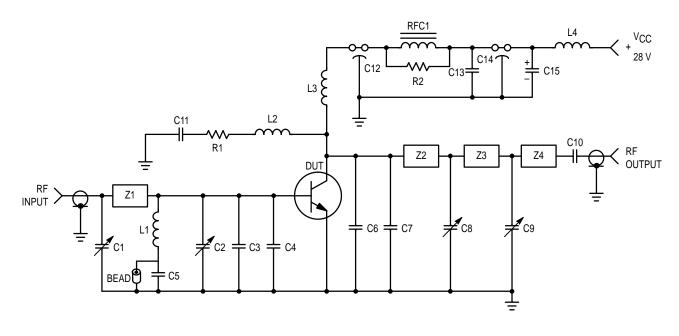
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (IC = 80 mAdc, IB = 0)	V(BR)CEO	30	_	_	Vdc
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 80 mAdc, V <sub>BE</sub> = 0)	V(BR)CES	60	_	_	Vdc
Emitter–Base Breakdown Voltage (IE = 8 mAdc, IC = 0)	V(BR)EBO	4	_	_	Vdc

- (1) This device is designed for RF operation. The total device dissipation rating applies only when the device is operated as an RF amplifier.
- (2) Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques.



# **ELECTRICAL CHARACTERISTICS** — **continued** ( $T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•	•	•	•	•
Collector–Base Breakdown Voltage (IC = 80 mAdc, IE = 0)	V(BR)CBO	60	_	_	Vdc
Collector Cutoff Current (V <sub>CB</sub> = 30 Vdc, I <sub>E</sub> = 0)	ICBO	_	_	5	mAdc
ON CHARACTERISTICS	•		•		
DC Current Gain (I <sub>C</sub> = 4 Adc, V <sub>CE</sub> = 5 Vdc)	hFE	20	_	80	_
DYNAMIC CHARACTERISTICS	-				
Output Capacitance (V <sub>CB</sub> = 28 Vdc, I <sub>E</sub> = 0, f = 1 MHz)	C <sub>ob</sub>	_	95	125	pF
FUNCTIONAL TESTS (Figure 1)					
Common–Emitter Amplifier Power Gain (V <sub>CC</sub> = 28 Vdc, P <sub>Out</sub> = 80 W, f = 470 MHz)	GPE	7.3	8.8	_	dB
Collector Efficiency (V <sub>CC</sub> = 28 Vdc, P <sub>Out</sub> = 80 W, f = 470 MHz)	η	50	60	_	%
Load Mismatch (V <sub>CC</sub> = 28 Vdc, P <sub>Out</sub> = 80 W, f = 470 MHz, VSWR = 30:1, All Phase Angles at Frequency of Test)	Ψ	No Degradation in Output Power			



Bead	Ferroxcube #56–590–65/3B	L3	3 Turns #18 AWG, 0.185" ID, Close Wound
C1, C2, C8, C9	0.8-20 pF, Johanson (JMC 5501)	L4	4 Turns #18 AWG, 0.185" ID, Close Wound
C3, C4, C6, C7	25 pF, 100 V, Underwood	RFC1	Ferroxcube VK200 19/4B
C5, C10	100 pF, 100 V, Underwood	R1, R2	10 Ω, 2.0 Watt Carbon
C11, C13	0.1 μF, Erie Redcap	<b>Z</b> 1	0.190" W x 2.5" L, Microstrip Lin
C12, C14	680 pF, Feedthru	Z2	0.190" W x 0.289" L, Microstrip Line
C15	1.0 μF, Tantalum	Z3	0.190" W x 0.55" L, Microstrip Line
L1	0.15 μH, Molded Choke	Z4	0.190" W x 0.325" L, Microstrip Line
L2	5 Turns #20 AWG, 0.185" ID, Close Wound	Board	Glass Teflon, t = 0.062", $\varepsilon_{\Gamma}$ = 2.56

Figure 1. 470 MHz Test Circuit

## **TYPICAL CHARACTERISTICS**

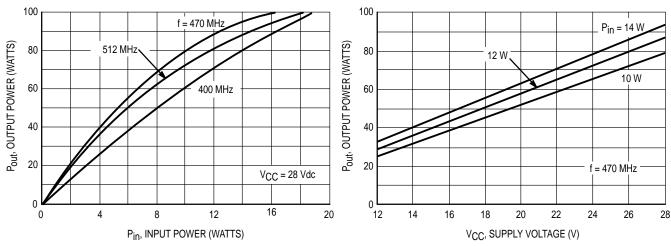


Figure 2. Output Power versus Input Power

Figure 3. Output Power versus Supply Voltage

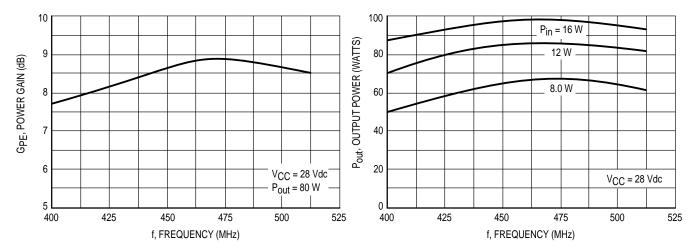
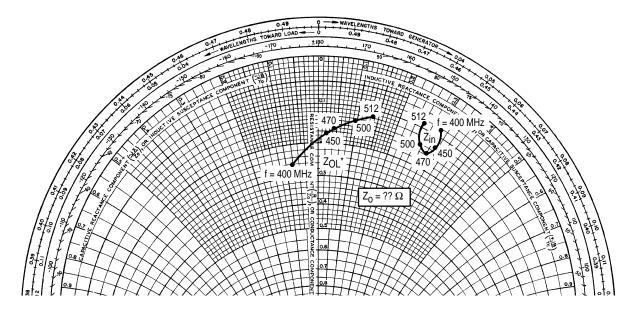


Figure 4. Power Gain versus Frequency

Figure 5. Output Power versus Frequency

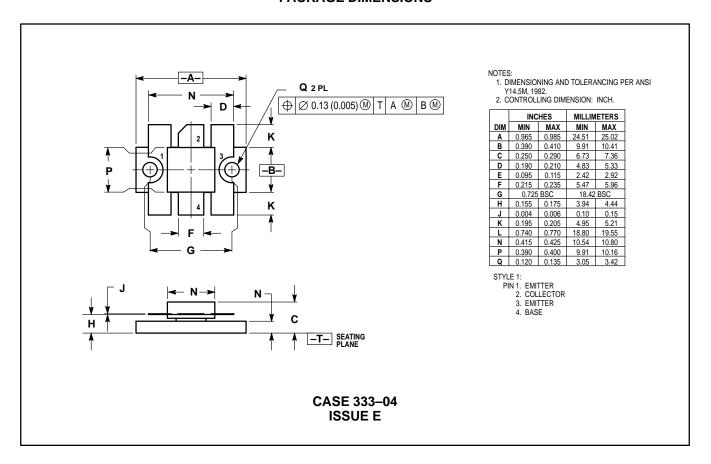


V <sub>CC</sub> = 28 V, P <sub>out</sub> = 80 W			
f	Z <sub>in</sub>	Z <sub>OL</sub> *	
MHz	Ohms	Ohms	
512	0.91 + j2.61	1.19 + j1.34	
500	1.47 + j2.71	1.33 + j0.96	
470	1.53 + j2.98	1.60 + j0.45	
450	1.27 + j3.09	1.70 + j0.25	
400	0.86 + j3.01	2.58 - j0.79	

 $Z_{OL}^{\star}$  = Conjugate of the optimum load impedance into which the device output operates at a given output power, voltage and frequency.

Figure 6. Series Equivalent Input/Output Impedance

#### **PACKAGE DIMENSIONS**



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